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IN THE CLAIMS:

Please cancel claims 22, 25, 29, 32, 23, 26, 30, 33 - 35, and 39 - 41. For convenience all claims are presented.

1 21. An inspection system comprising: 2 an inspection apparatus for detecting positions and sizes of particles or 3 pattern defects on an object to be inspected; 4 an image taking apparatus for taking images of said particles or said 5 pattern defects as detected by said inspection apparatus; and 6 an analysis unit operatively coupled to said inspection apparatus and said 7 image taking apparatus, said analysis unit including: 8 a storage device for storing therein inspection data produced by 9 said inspection apparatus and position information of regions of a circuit pattern to be 10 formed on said object; 11 a calculation device for identifying particles and pattern defects / 12 that are correspondingly positioned in said regions, and calculating failure probabilities for said particles and said pattern defects positioned in said regions based on their sizes; 13 14 and 15 a selection device for selecting particles or pattern defects whose 16 calculated failure probabilities are greater than or equal to a predetermined threshold. 22 - 23. These claims have been canceled in response to a restriction. 1 24. The inspection system according to claim 21, wherein said regions 2 are circuit blocks as formed within an LSI chip. 25 - 26. These claims have been canceled in response to a restriction.

27. The inspection system according to claim 21, further comprising a simulation device for generating virtual defects at random positions with respect to circuit graphics obtainable from mask layout data forming said circuit pattern, and computing

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extraction step.

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4	said failure probabilities from connection relationships of said circuit graphics and said
5	defects.
1	28. The inspection system according to claim 21, wherein said position
2	information of said regions is generated from mask layout data forming an LSI chip.
	29 - 30. These claims have been canceled in response to a restriction.
1	31. The inspection system according to claim 24, wherein said position
2	information of said circuit blocks is generated from mask layout data forming an LSI
3	chip.
	32 - 35. These claims have been canceled in response to a restriction.
1	36. A method for manufacturing semiconductor devices comprising
2	the steps of:
3	a fabrication step for forming circuit patterns on or over a wafer, said
4	circuit patterns constituting a plurality of semiconductor chips;
5	an inspection step for detecting positions and sizes of particles or pattern
6	defects of said wafer;
7	identifying positions and sizes of those of said particles or said pattern
8	defects located in a region of said circuit patterns that constitute one of said
9	semiconductor chips;
10	a calculation step for calculating failure probabilities based on sizes of
11	said pattern defects in said region;
12	an extraction step for extracting positions of said particles or said pattern
13	defects with calculated failure probabilities greater than or equal to a predefined
14	threshold; and
15	producing images of said particles or said pattern defects extracted at said

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- 1 37. A method for manufacturing semiconductor devices according to claim 36, wherein said regions are circuit blocks within an LSI chip.
- 1 38. A method for manufacturing semiconductor devices according to 2 claim 37, wherein said LSI chip is a system LSI and said circuit blocks include memory 3 portions and logic portions.
 - 39 41. These claims have been canceled in response to a restriction.